

MA2B064

Silicon planar type trigger device

Thyristor element

■ Features

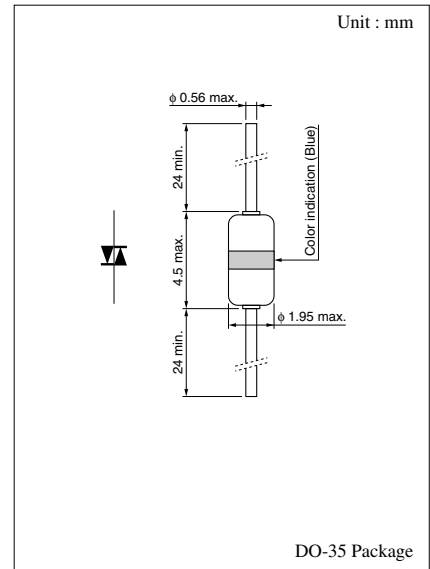
- Satisfactory symmetry of V_{BO}
- Large V_O and small I_{BO}

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Average total power dissipation	$P_{(AV)}$	150	mW
Peak current*1	I_{PM}	2.0	A
Operating ambient temperature*2	T_{opr}	100	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

Note) *1 : $T_a < 50^\circ\text{C}$, $t = 10 \mu\text{s}$, repetitive frequency 60 Hz

*2 : Maximum ambient temperature during operation



Marking Symbol: MA2B064

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakover current	I_{BO}	$V = V_{BO}$			50	μA
Breakover voltage*1	V_{BO}	$I = I_{BO}$	28		36	V
Output voltage*1	V_O		4	7		V
Temperature coefficient of breakover voltage	—			0.1		$\% / ^\circ\text{C}$
Breakover voltage deviation*2	ΔV_{BO}				3.5	V

Note) 1. Rated input/output frequency: 100 MHz

2. *1 : Measurement of V_{BO} and V_O

*2 : Symmetry of V_{BO}

